

Summary

V _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	24mΩ @V _{GS} = -4.5V	-6.6 A
	31mΩ @V _{GS} = -2.5V	-5.8 A

Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

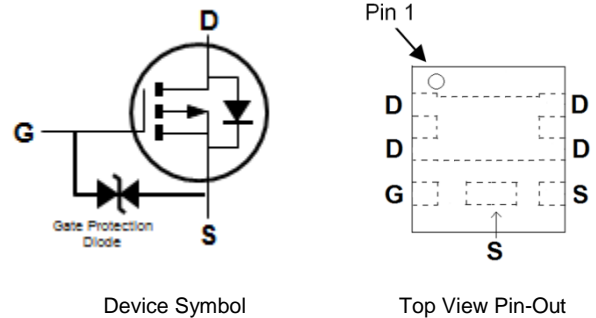
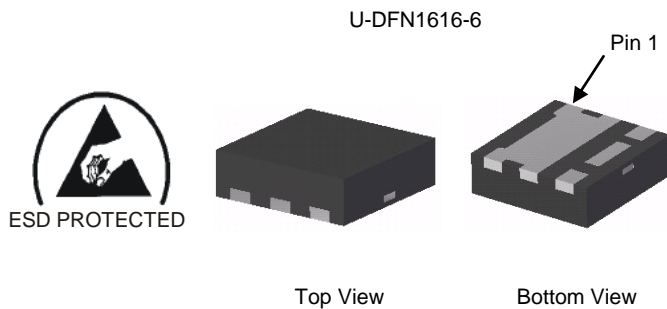
- Power Management Functions
- Analog Switches

Features and Benefits

- Typical Off Board Profile of 0.575mm - Ideally Suited for Thin Applications
- Low R_{DS(ON)} - Minimizes Conduction Losses
- PCB Footprint of 2.56mm²
- ESD Protected Gate 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

- Case: U-DFN1616-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (NiPdAu Finish over Copper Leadframe).
- Terminals: Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.04 grams (Approximate)

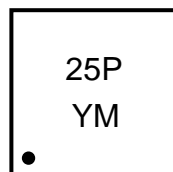


Ordering Information (Note 4)

Product	Case	Packaging
DMP2035UFCL-7	U-DFN1616-6	3,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



25P = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6)	Steady State	T _A = +25°C T _A = +70°C	I _D	-6.6 -5.3	A
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)(Note 7)			I _{DM}	-40	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-1.7	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.74	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	169	°C/W
Power Dissipation (Note 6)	P _D	1.6	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	79	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1.0	µA	V _{DS} = -16V, V _{GS} = 0V
Zero Gate Voltage Drain Current T _J = +150°C (Note 8)	I _{DSS}	-	-	-100	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	µA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	-	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	19	24	mΩ	V _{GS} = -4.5V, I _D = -8.0A
			24	31		V _{GS} = -2.5V, I _D = -7.0A
			31	45		V _{GS} = -1.8V, I _D = -6.0A
Diode Forward Voltage	V _{SD}	-0.5	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	1,610	2,200	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	-	157	240	pF	
Reverse Transfer Capacitance	C _{rss}	-	145	220	pF	
Gate Resistance	R _g	-	9.45	14.5	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -8V)	Q _g	-	29	44	nC	V _{DS} = -10V, I _D = -4A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	-	15.4	21	nC	
Gate-Source Charge	Q _{gs}	-	2.5	3.8	nC	
Gate-Drain Charge	Q _{gd}	-	3.3	5	nC	V _{DS} = -20V, V _{GS} = -10V, R _G = 6.0Ω, I _D = -6A
Turn-On Delay Time	t _{D(ON)}	-	16.8	34	ns	
Turn-On Rise Time	t _R	-	12.4	25	ns	
Turn-Off Delay Time	t _{D(OFF)}	-	94.1	188	ns	
Turn-Off Fall Time	t _F	-	42.4	85	ns	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Repetitive rating, pulse width limited by junction temperature.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

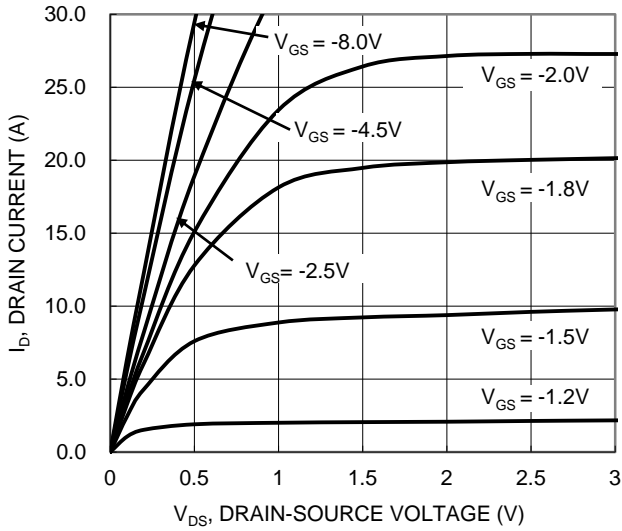


Figure 1. Typical Output Characteristic

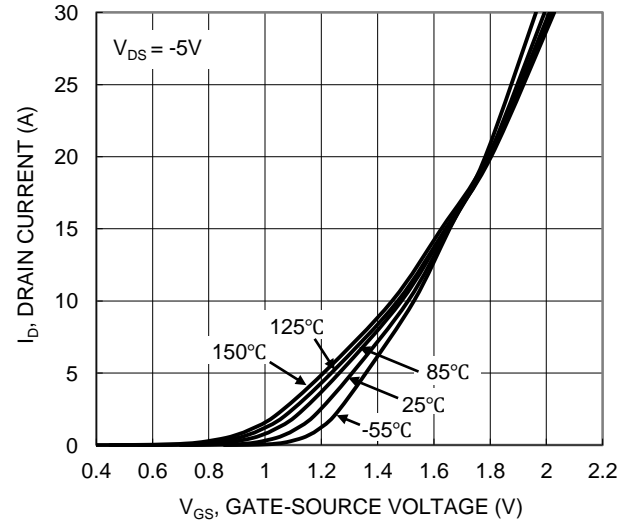


Figure 2. Typical Transfer Characteristic

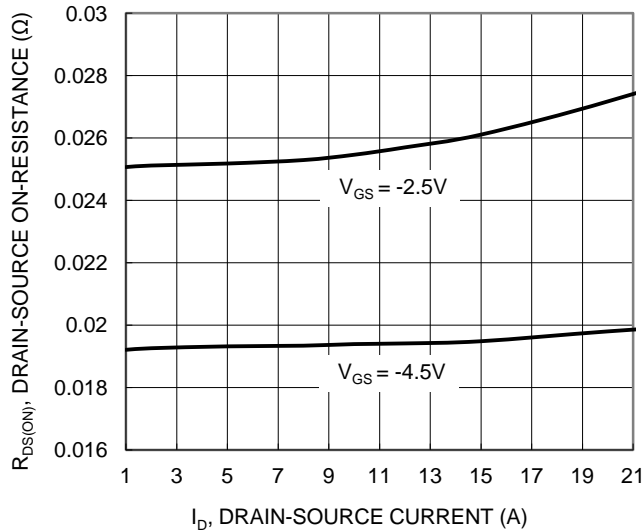


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

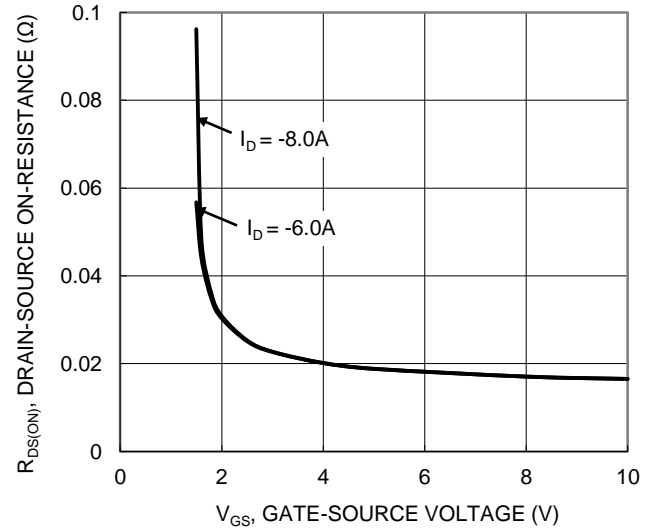


Figure 4. Typical Transfer Characteristic

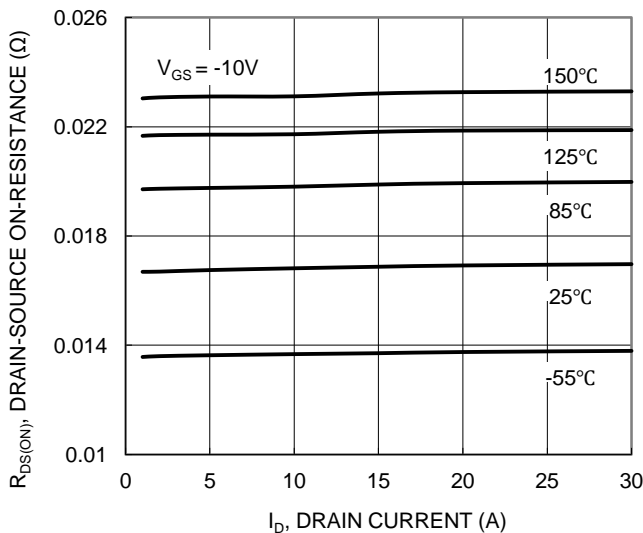


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

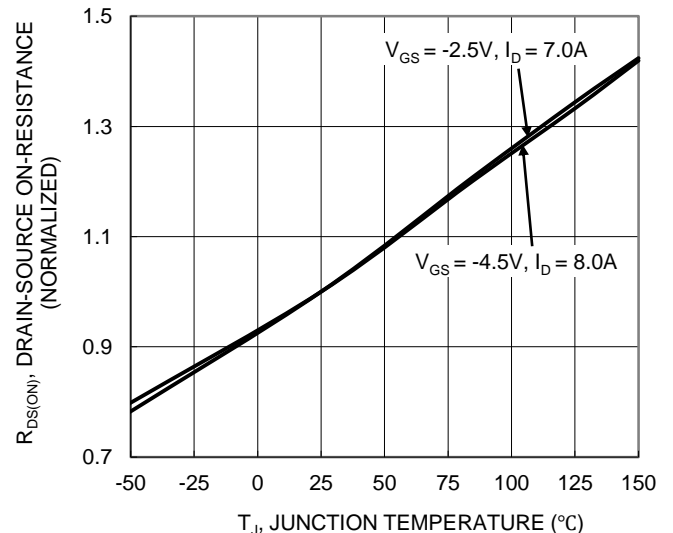


Figure 6. On-Resistance Variation with Junction Temperature

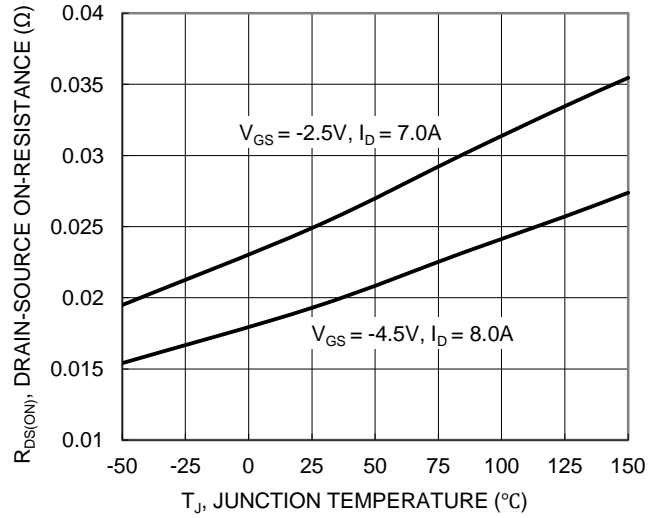


Figure 7. On-Resistance Variation with Junction Temperature

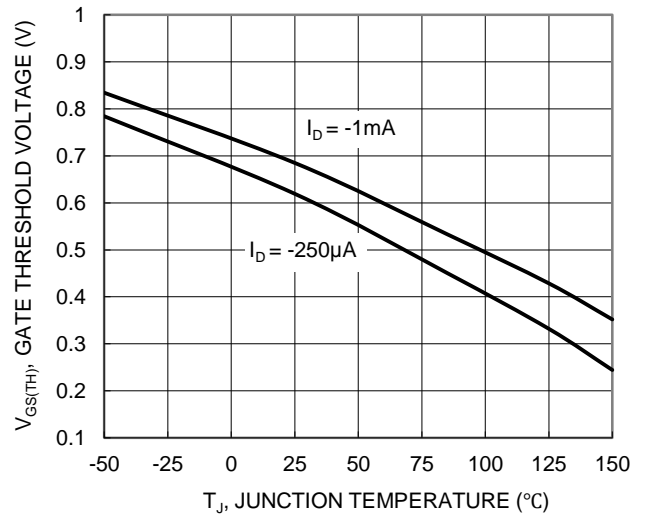


Figure 8. Gate Threshold Variation vs. Junction Temperature

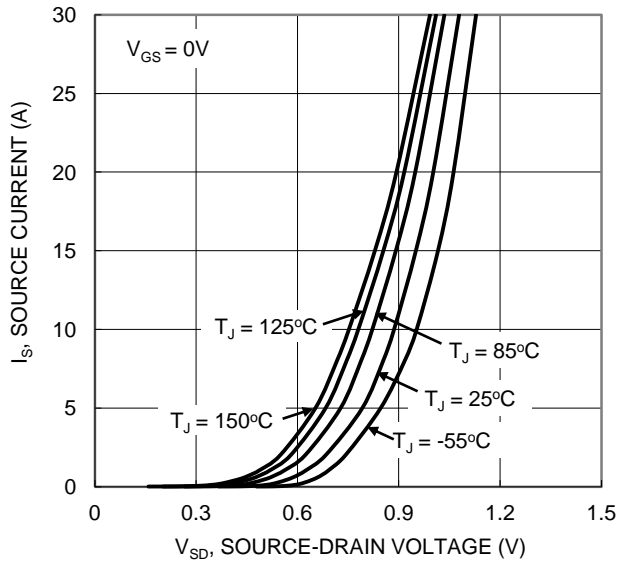


Figure 9. Diode Forward Voltage vs. Current

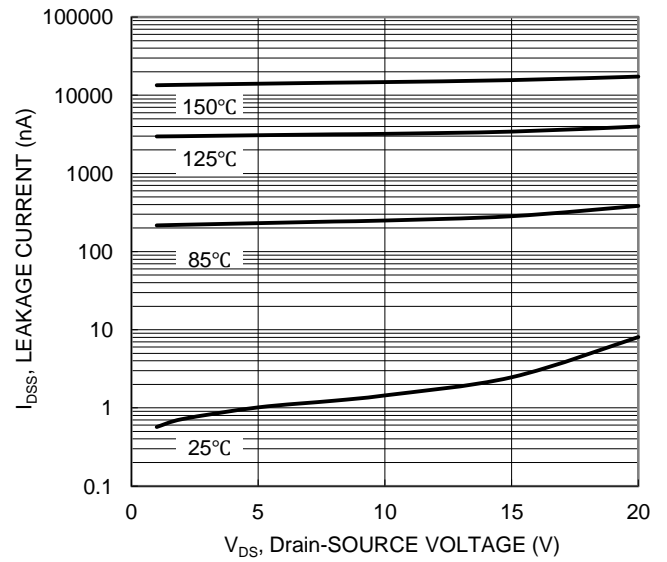


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

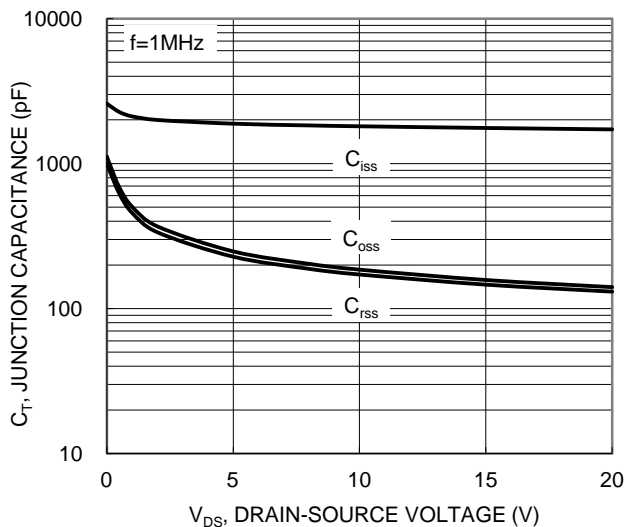


Figure 11. Typical Junction Capacitance

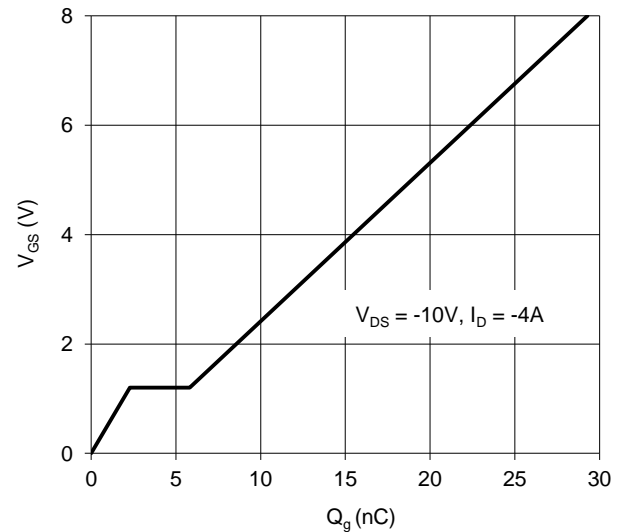
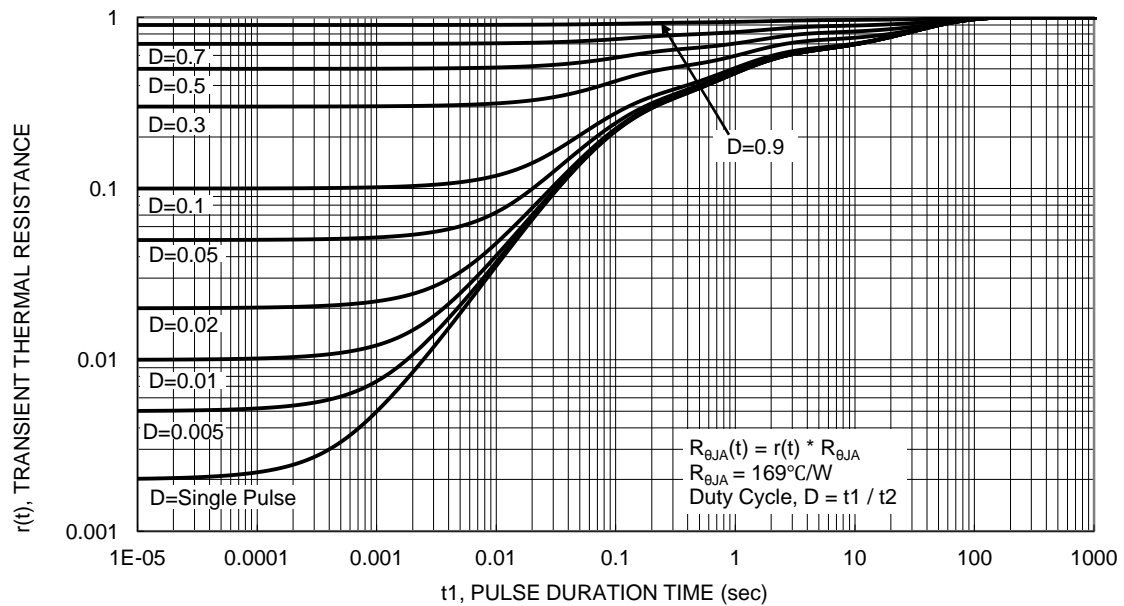
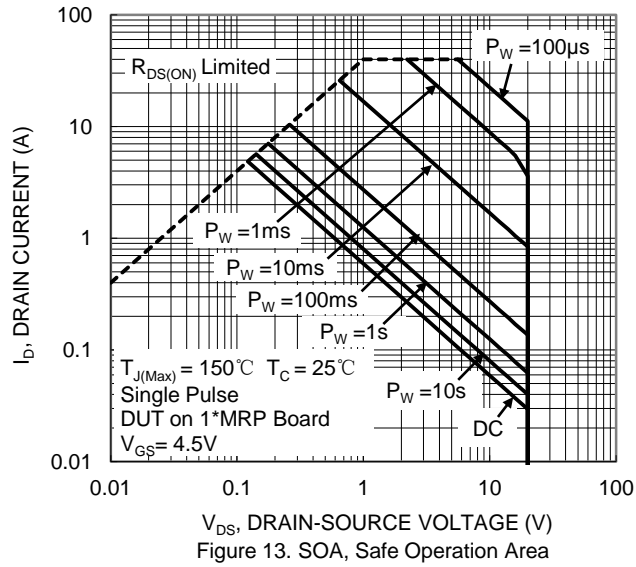
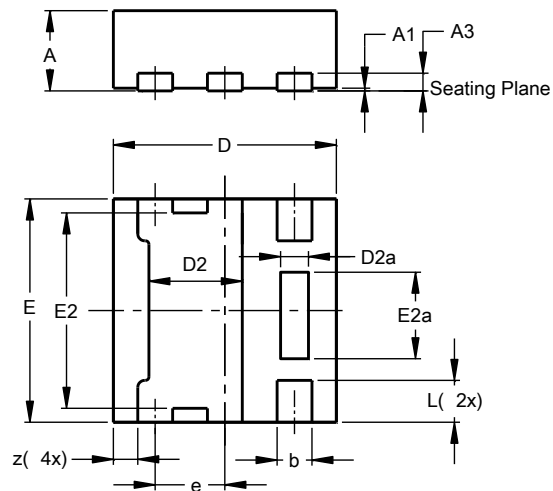


Figure 12. Gate Charge



Package Outline Dimensions

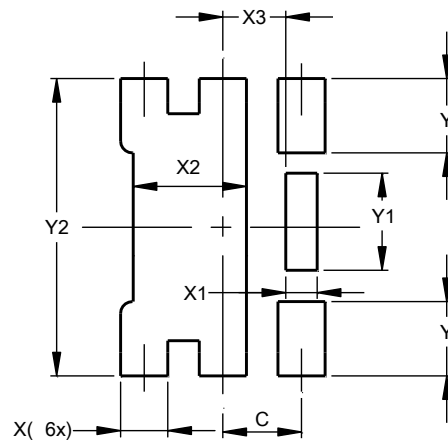
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN1616-6 (Type K)			
Dim	Min	Max	Typ
A	0.55	0.60	0.575
A1	0.00	0.05	0.02
A3	--	--	0.13
b	0.20	0.30	0.25
D	1.55	1.65	1.60
D2	0.57	0.77	0.67
D2a	0.10	0.30	0.20
e	--	--	0.50
E	1.55	1.65	1.60
E2	1.30	1.50	1.40
E2a	0.52	0.72	0.62
L	0.25	0.35	0.30
z	--	--	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.500
X	0.300
X1	0.200
X2	0.720
X3	0.400
Y	0.475
Y1	0.620
Y2	1.900

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